Silicon Switching Diode

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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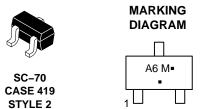
MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	V
Recurrent Peak Forward Current	I _R	200	mA
Peak Forward Surge Current Pulse Width = 10 μs	I _{FM(surge)}	500	mA
Total Power Dissipation, One Diode Loaded T _A = 25°C Derate above 25°C Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	P _D	200 1.6	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient One Diode Loaded Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	$R_{ hetaJA}$	625	°C/W



A6 = Specific Device Code

M = Date Code ■ = Pb-Free Package

(*Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS16WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
SBAS16WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NSVBAS16WT3G	SC-70 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage (I _F = 1.0 mA) (I _F = 10 mA) (I _F = 50 mA) (I _F = 150 mA)	V _F	- - - -	715 866 1000 1250	mV
Reverse Current (V _R = 100 V) (V _R = 75 V, T _J = 150°C) (V _R = 25 V, T _J = 150°C)	I _R	- - -	1.0 50 30	μΑ
Capacitance (V _R = 0, f = 1.0 MHz)	C _D	_	2.0	pF
Reverse Recovery Time (I _F = I _R = 10 mA, R _L = 50 Ω) (Figure 1)	t _{rr}	_	6.0	ns
Stored Charge (I _F = 10 mA to V_R = 6.0 V, R_L = 500 Ω) (Figure 2)	QS	_	45	PC
Forward Recovery Voltage ($I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$) (Figure 3)	V _{FR}	_	1.75	V

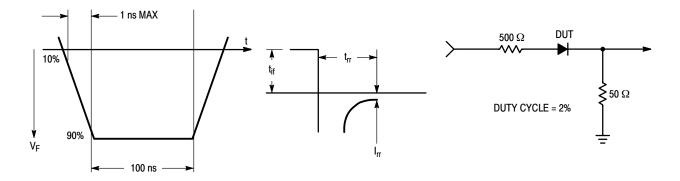


Figure 1. Reverse Recovery Time Equivalent Test Circuit

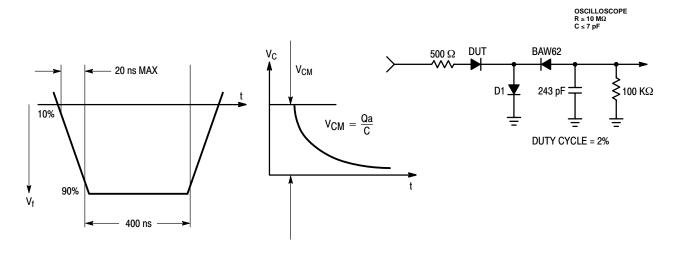


Figure 2. Stored Charge Equivalent Test Circuit

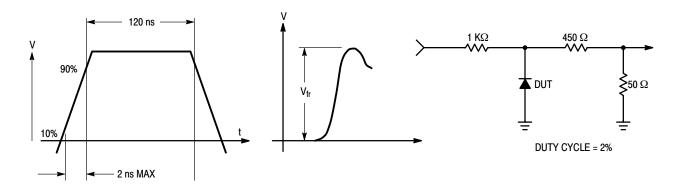


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

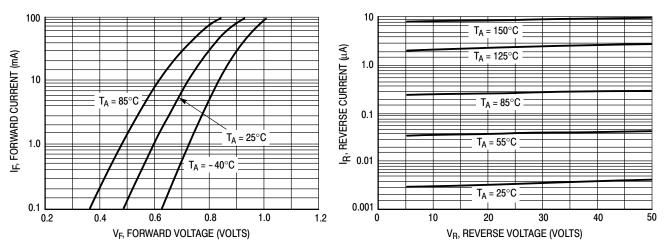


Figure 4. Forward Voltage

Figure 5. Leakage Current

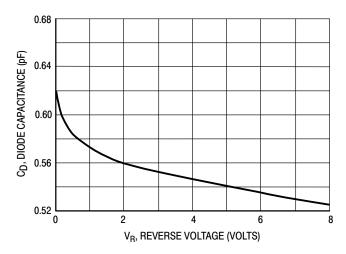


Figure 6. Capacitance





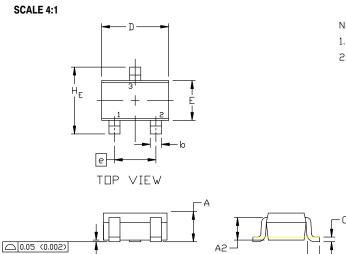
SC-70 (SOT-323) **CASE 419** ISSUE R

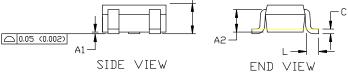
DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				TNICHES	
	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF		0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





GENERIC MARKING DIAGRAM



= Specific Device Code XX

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

0.65 [0.025]
1.90 [0.075]
0.90 [0.035]
0.70 [0.028]

For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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